Supporting Information

Wet-etching Fabrication of Flexible and Transparent Silicon

Frameworks for Imperceptible Wearable Electronics

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Supplementary Figures



Figure S1. Photographs of stainless-steel fixtures with a silicon wafer fixed in the middle. (a) A top-view photograph. (b) A side-view photograph.



Figure S2. Photographs of a single-thinned silicon wafer. (a) The thinned side. (b) The protected side.



Figure S3. SEM images of sc-SiFs obtained by reactive ion etching (RIE) and wet etching. (a) Sidewalls of sc-SiFs obtained by RIE are rough. (b) Sidewalls of sc-SiFs obtained by wet etching are smooth.



Figure S4. The images of bubbling along the fixture edge in the alkali etching process.



Figure S5. Single-sided thinning of a 4-inch silicon wafer. (a) The 4-inch silicon wafer clamped with large SS fixtures. (b) Photograph of the 4-inch silicon wafer after single-side thinning.



Figure S6. The relative change in resistance of the sc-SiFs sensor under different pressures.